

20V P沟道功率MOSFET

UM8517P6 SOT363

描述

UM8517P6 是低阈值 P 沟道 MOSFET，具有极低的导通电阻。这一优势为设计师提供了适用于电池和负载管理应用的极高效器件。UM8517P6 采用节省空间的小型 SOT363 封装。

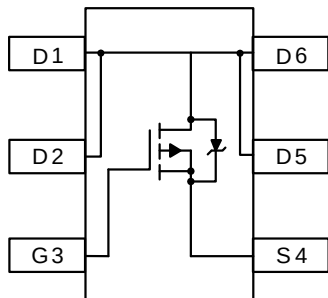
应用

- 电池组
- 电池供电的便携式设备
- 手机和无线电话

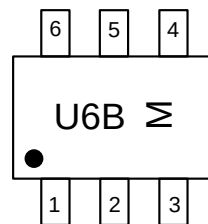
特性

- 漏源电压（最大）：-20V
- 低导通电阻：
 $R_{DS(ON)} < 130m\Omega @ V_{GS} = -4.5V, I_D = -2.8A$
 $R_{DS(ON)} < 150m\Omega @ V_{GS} = -2.5V, I_D = -2.0A$
- 持续漏极电流（最大）：-2.8A@25℃

引脚配置



顶部视图



M: Month Code
UM8517P6
SOT363

Ordering Information

Part Number	Packaging Type	Marking Code	Shipping Qty
UM8517P6	SOT363	U6B	3000pcs/7 Inch Tape & Reel

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	-2.8	A
I_{DM}	Drain Current Pulsed	-9	A
P_D	Power Dissipation	1	W
T_J	Junction Temperature	-55~150	℃
T_{STG}	Storage Temperature	-55~150	℃
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	℃/W

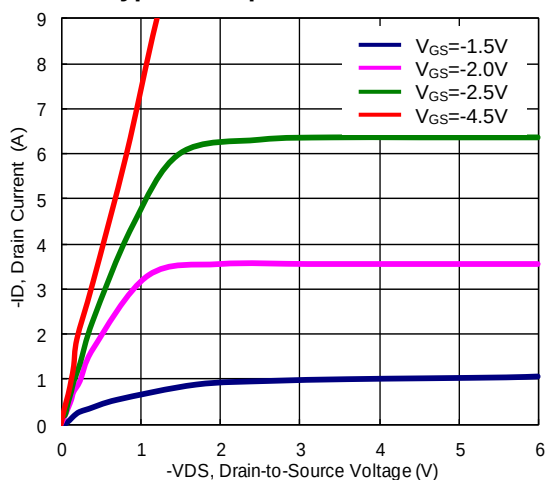
Electrical Characteristics

(T_A=25 °C, unless otherwise noted)

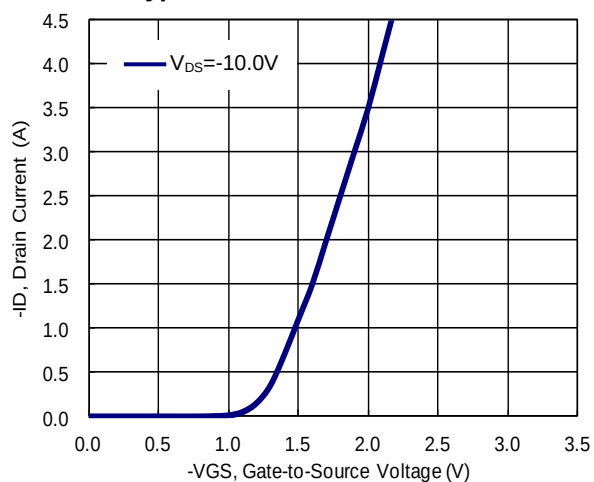
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V			-1	μA
I _{GSS}	Gate-to-Source Leakage Current	V _{GS} = ±12V, V _{DS} =0V			±100	nA
On Characteristics						
R _{DS(ON)}	Static Drain-to-Source On-Resistance	V _{GS} =-4.5V, I _D =-2.8A		110	130	mΩ
		V _{GS} =-2.5V, I _D =-2.0A		130	150	
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =-250μA	-0.4	-0.7	-1	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-2.0A		6		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1.0MHz		405		pF
C _{oss}	Output Capacitance			75		
C _{rss}	Reverse Transfer Capacitance			55		
Switching Characteristics						
Q _{g(TH)}	Threshold Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-1.0A		3.3		nC
Q _{GS}	Gate-Source Charge			0.7		
Q _{GD}	Gate-Drain Charge			1.3		
td(on)	Turn-on Delay Time	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-1.0A R _{GEN} =10Ω		11		ns
tr	Rise Time			35		
td(off)	Turn-off Delay Time			30		
tf	Fall Time			10		
Drain-Source Diode Characteristics and Maximum Ratings						
V _{SD}	Forward Diode Voltage	V _{GS} =0V, I _S =-1A		-0.7	-1.2	V

Typical Characteristics

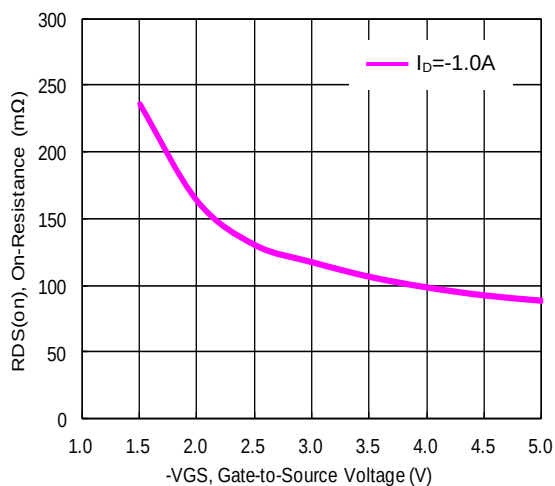
Typical Output Characteristics



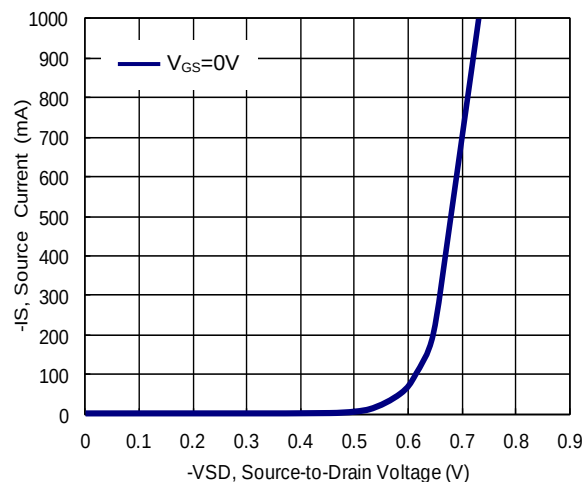
Typical Transfer Characteristics



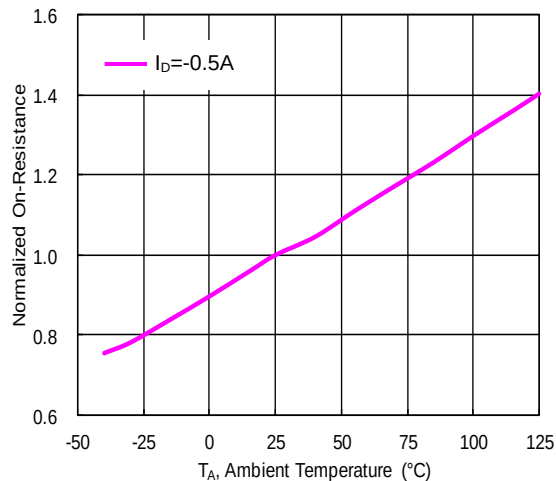
On-Resistance vs. Gate-to-Source Voltage



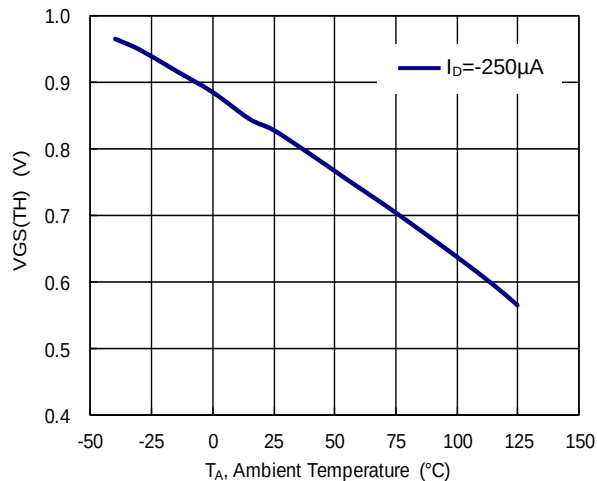
Diode Forward Voltage vs. Current



On-Resistance vs. Ambient Temperature



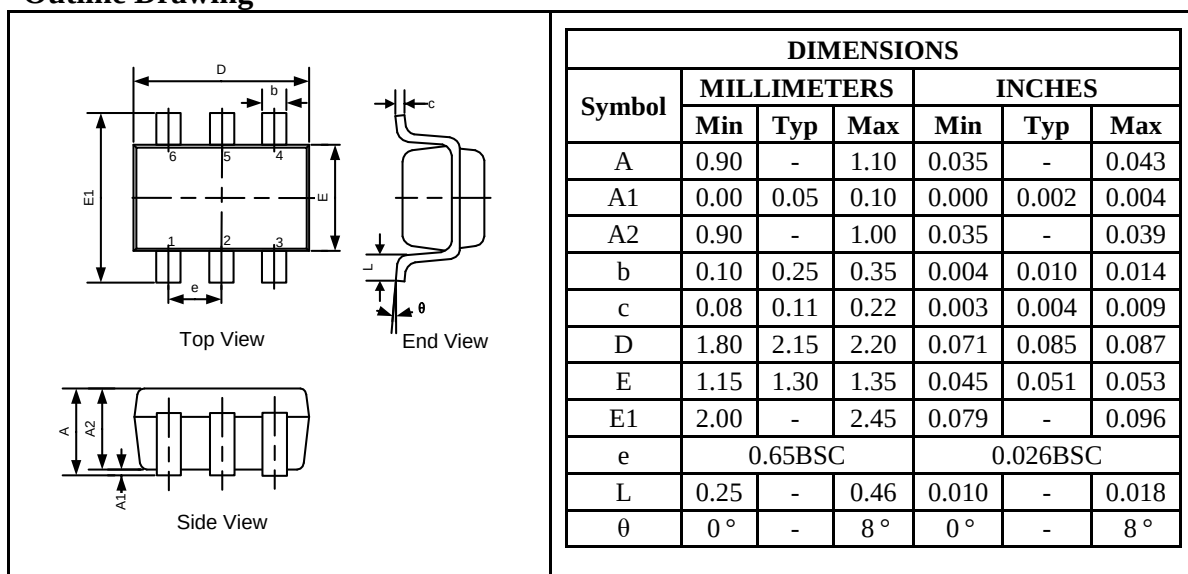
Threshold Voltage vs. Ambient Temperature



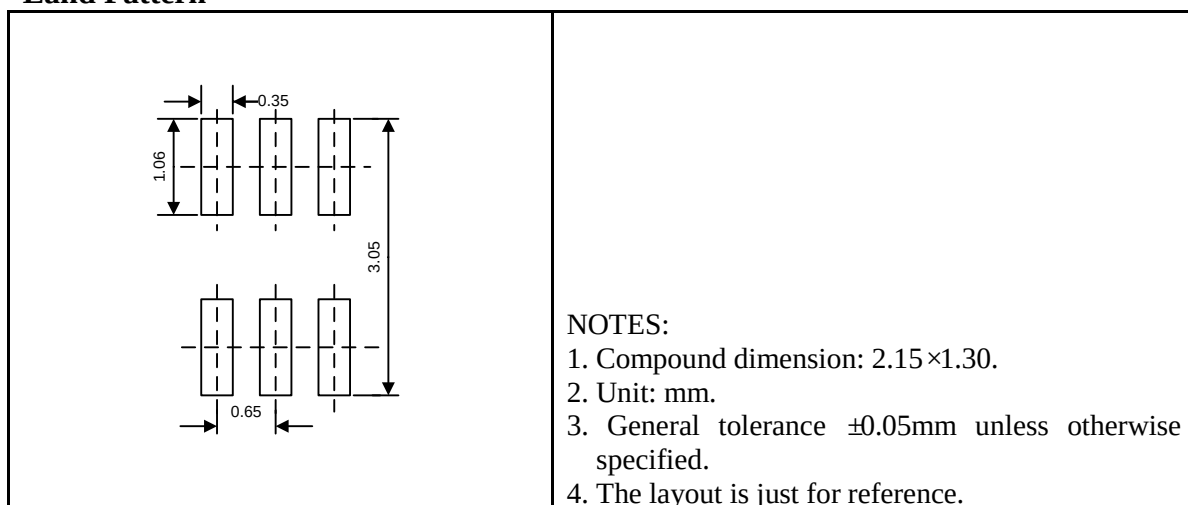
Package Information

UM8517P6 SOT363

Outline Drawing



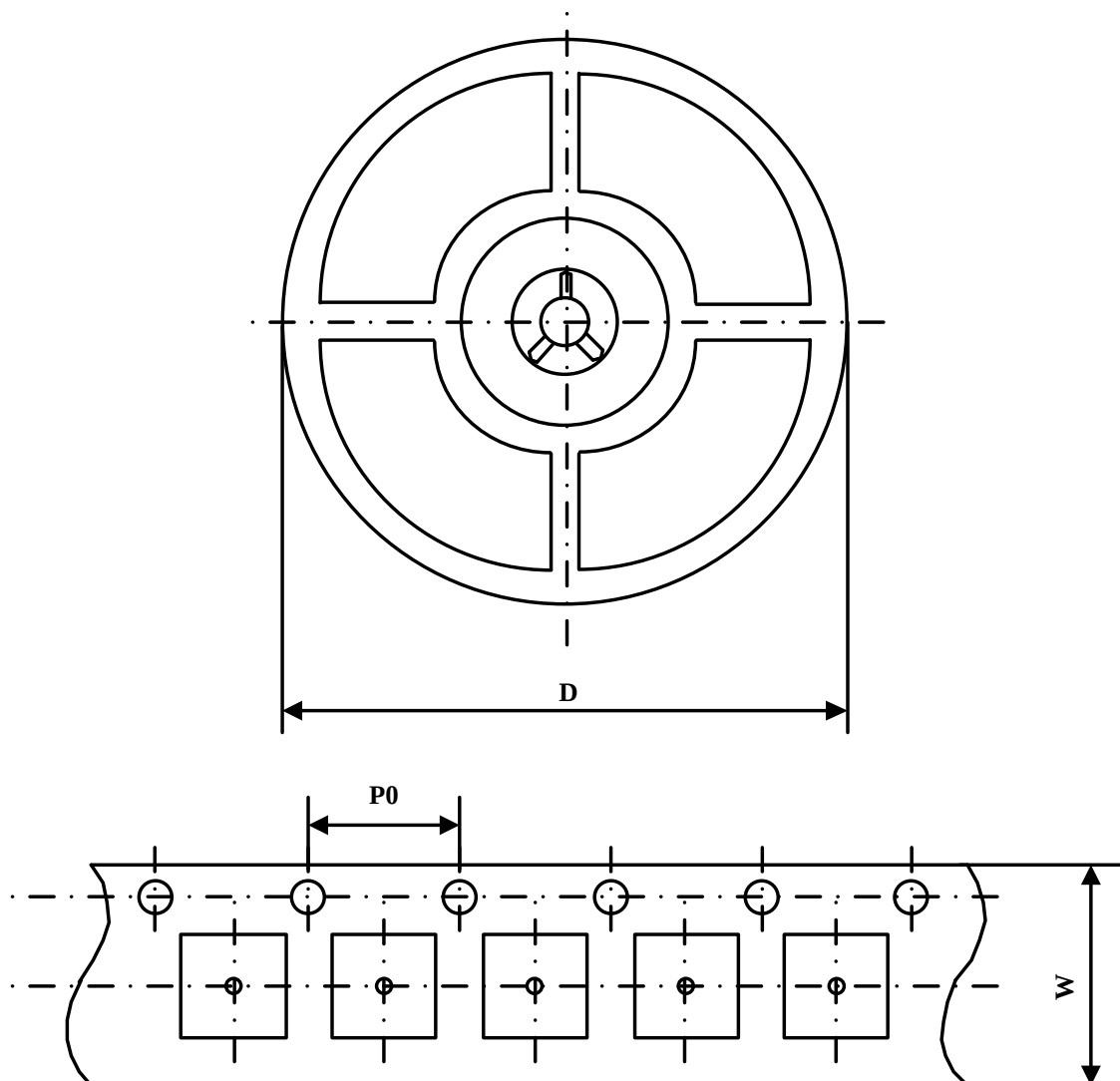
Land Pattern



Tape and Reel Orientation



Packing Information



Part Number	Package Type	Carrier Width(W)	Pitch(P0)	Reel Size(D)
UM8517P6	SOT363	8 mm	4 mm	180 mm

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